adding to the chamber a second gas containing a chemical element intended, together with the element contained in the first gas and able to contaminate copper, to form said dielectric material, the second gas being able to react with the first gas to give the deposit of dielectric material,

performing the deposit of dielectric material from the first gas and the second gas, the method also comprising a step for adding a third gas able to prevent the contamination of copper by said element contained in the first gas.

20. The method according to claim 19, in which the deposit chamber permitting plasma assisted Chemical Vapour Deposition (PECVD), the method comprises a step for lighting the plasma to make the deposit of dielectric material from the first gas and the second gas.

21. The method according to claim 19, in which the first gas is silane, the contaminating element being Si.

22. The method according claim 19, in which said chemical element of the second gas is nitrogen.

23. The method according to claim 19, in which the 5 second gas is nitrogen.

24. The method according to claim 19, in which the third gas contains oxygen and/or nitrogen and/or carbon.

25. The method according to claim 24, in which the third gas is chosen from the group made up of N_xO_y, C_xH_y, a xN_2+yH_2 mixture or a xO_2+yN_2 mixture.

26. The method according to claim 24, in which the third gas is chosen from the group made up of NH_3, N_2O, CH_4 and C_2H_6.

27. The method according to claim 19, in which the first, second and third gases are also added before lighting of the plasma, the flow rates of the first, second and third gases,

the energy required for depositing and the time of formation of the deposit being adjusted in relation to the desired thickness of the dielectric material and its desired physical properties.

28. The method according to claim 20, in which the steps are conducted in the following order:

placing the structure in the deposit chamber,

adding the third gas to the deposit chamber, the third gas being chosen to reduce the oxides present on the surface of the copper,

lighting a plasma of third gas in the deposit chamber in order to reduce said oxides, adding the first and second gases to the deposit chamber, adjustment of the flow rates of the first, second and third gases, of the energy required for the deposit and the formation time of the deposit in relation to the desired thickness of the dielectric material and its desired physical properties.

29. The method according to claim 28, in which the third gas is ammonia.

30. The method according to claim 19, in which for the purpose of obtaining a dielectric material in SiN, the first gas is silane, said chemical element of the second gas is nitrogen and the third gas is ammonia.

31. The method according to claim 19, in which the formation of the dielectric material is made under a temperature of between 100 and 600°C.

32. A method for depositing a dielectric material on copper apparent on the surface of a structure, entailing the following steps:

placing the structure in a deposit chamber of CVD type (Chemical Vapour Deposition),

adding to the chamber a gas forming a precursor for the formation of the dielectric material and containing a first element able to contaminate copper and a second element able to combine with the first element to give the dielectric material,

making the deposit of dielectric material by combining the first element and the second element,

the method also comprising a step for adding an additional gas able to prevent the contamination of the copper by said element contained in the precursor gas.

33. The method according to claim 32, in which the deposit chamber permitting plasma assisted Chemical Vapour Deposition (PECVD), the method comprises a plasma lighting stage to make the deposit of dielectric material from the precursor gas.

34. The method according to claim 32, in which in order to obtain a dielectric material in SiC said gas forming a precursor is trimethylsilane.

35. Application of the method according to claim 19 to the depositing of a copper diffusion barrier layer on the surface of a structure containing at least one conductor line in copper.

36. Application of the method according to claim 19 for the depositing of copper-diffusion barrier layers at the time of fabricating interconnection levels in copper on semiconductor devices.--